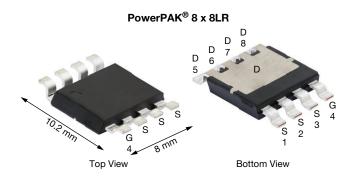


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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

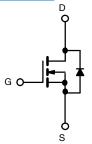


PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0015			
I <sub>D</sub> (A)	372			
Configuration	Single			

## **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>a</sub> and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 8 x 8LR
Lead (Pb)-free and halogen-free	SQJQ148ER (for detailed order number please see <a href="https://www.vishay.com/doc?79776">www.vishay.com/doc?79776</a> )

ABSOLUTE MAXIMUM RATING	S (T <sub>C</sub> = 25 °C, unles	s otherwise noted	l)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		$V_{DS}$	40	.,	
Gate-source voltage		$V_{GS}$	± 20	V	
Continuous drain current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	372		
	T <sub>C</sub> = 125 °C		214		
Continuous source current (diode conduction)		I <sub>S</sub>	360	Α	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	670		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	46		
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	105	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	D	394	W	
	T <sub>C</sub> = 125 °C	- P <sub>D</sub>	131		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) <sup>d</sup>			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient P	CB mount c	$R_{thJA}$	44	°C/W	
Junction-to-case (drain)		$R_{thJC}$	0.38		

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \mu A$		40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		2	3	3.5	1 °
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	200	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	100	-	=.	Α
Drain-source on-state resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.00125	0.0015	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0025	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0031	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 60 A		-	120	=.	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 25 V, f = 1 MHz	-	4170	5750	pF
Output capacitance	C <sub>oss</sub>			-	1566	2193	
Reverse transfer capacitance	C <sub>rss</sub>	]		-	131	184	
Total gate charge <sup>c</sup>	Qg		= 10 V V <sub>DS</sub> = 20 V, I <sub>D</sub> = 20 A	-	68	102	nC
Gate-source charge c	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$		-	20	-	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	15	-	1
Gate resistance	$R_g$	f = 1 MHz		0.8	1.6	2.4	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 20 \text{ V, } R_L = 1  \Omega$ $I_D \cong 20 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1  \Omega$		-	17	26	
Rise time <sup>c</sup>	t <sub>r</sub>			-	88	132	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	30	45	
Fall time <sup>c</sup>	t <sub>f</sub>			-	12	18	
Source-Drain Diode Ratings and Cha	aracteristics <sup>b</sup>						
Reverse recovery time	t <sub>rr</sub>	V <sub>DD</sub> = 32 V, I <sub>FM</sub> = 15 A, di/dt = 100 A/μs		-	47	94	ns
Reverse recovery charge	Q <sub>rr</sub>			-	47	94	nC
Reverse recovery current	I <sub>RM</sub>			-	-	1.8	Α
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	1600	Α
Forward voltage	V <sub>SD</sub>	$I_F = 50 \text{ A}, V_{GS} = 0$		-	0.8	1.1	V

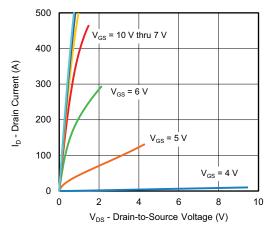
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

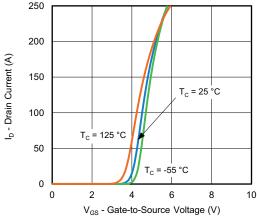
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



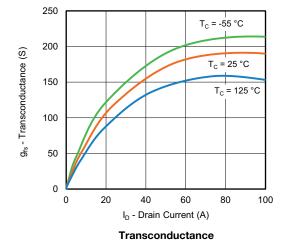
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

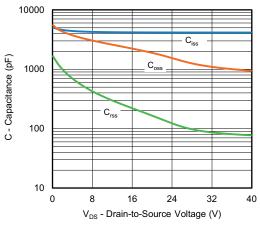


## **Output Characteristics**

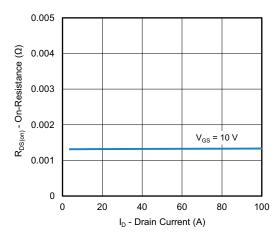


Transfer Characteristics

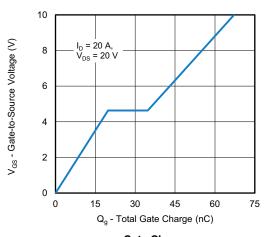




Capacitance

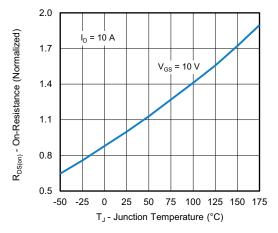


**On-Resistance vs. Drain Current** 

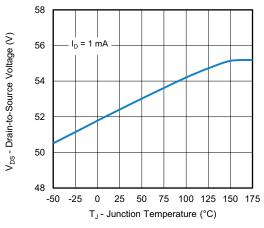




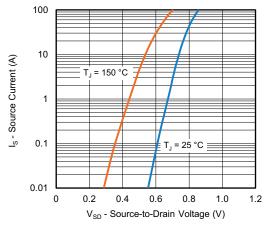
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



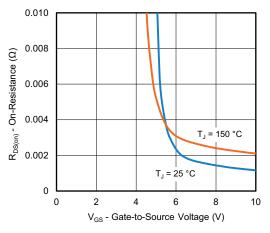
On-Resistance vs. Junction Temperature



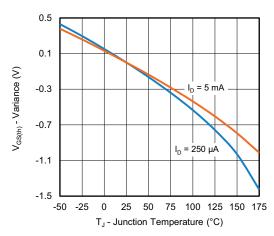
Drain Source Breakdown vs. Junction Temperature



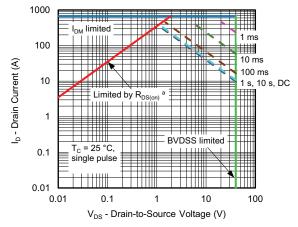
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Safe Operating Area

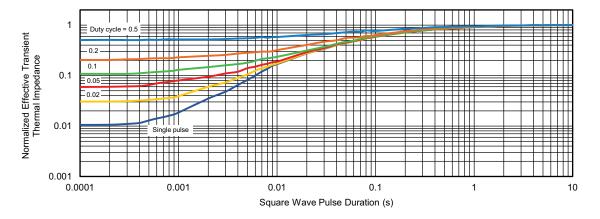
## Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

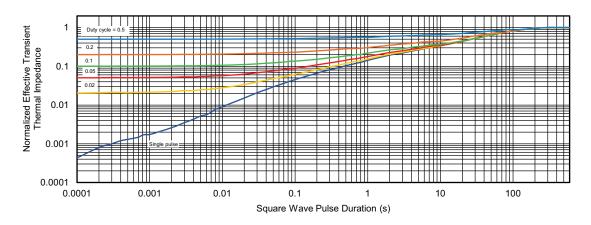
For technical questions, contact: automostech



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



## Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?66839">www.vishay.com/ppg?66839</a>.



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